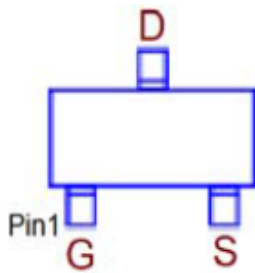


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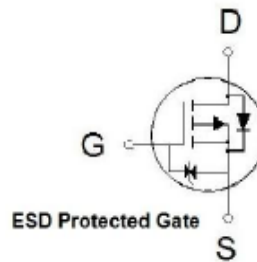
P-Channel Enhancement Mode MOSFET

PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
-20V	520mΩ @ $V_{GS} = -4.5V$	-0.5A



SOT-723



ABSOLUTE MAXIMUM RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Gate-Source Voltage		V_{GS}	± 12	V
Continuous Drain Current ²	$T_A = 25\text{ }^{\circ}\text{C}$	I_D	-0.5	A
	$T_A = 70\text{ }^{\circ}\text{C}$		-0.4	
Pulsed Drain Current ¹		I_{DM}	-1	
Power Dissipation	$T_A = 25\text{ }^{\circ}\text{C}$	P_D	0.25	W
	$T_A = 70\text{ }^{\circ}\text{C}$		0.16	
Operating Junction & Storage Temperature Range		T_J, T_{stg}	-55 to 150	$^{\circ}\text{C}$

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient	$R_{\theta JA}$		500	$^{\circ}\text{C} / \text{W}$

¹Limited by maximum junction temperature.

²Limited by package.

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ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNITS
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-20			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-0.4	-0.96	-1.2	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 12V$			± 30	μA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -16V, V_{GS} = 0V$			-1	μA
		$V_{DS} = -10V, V_{GS} = 0V, T_J = 75\text{ }^{\circ}C$			-10	
Drain-Source On-State Resistance ¹	$R_{DS(ON)}$	$V_{GS} = -4.5V, I_D = -450mA$		500	520	m Ω
		$V_{GS} = -2.5V, I_D = -100mA$		770	800	
Forward Transconductance ¹	g_{fs}	$V_{DS} = -5V, I_D = -450mA$		1.6		S
DYNAMIC						
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = -10V, f = 1MHz$		48		pF
Output Capacitance	C_{oss}			18		
Reverse Transfer Capacitance	C_{rss}			10		
Turn-On Delay Time ²	$t_{d(on)}$	$V_{DD} = -10V, I_D \cong -450mA$ $V_{GS} = -4.5V, R_{GEN} = 5.1\Omega$		17		nS
Rise Time ²	t_r			30		
Turn-Off Delay Time ²	$t_{d(off)}$			76		
Fall Time ²	t_f			46		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T _J = 25 °C)						
Continuous Current	I _S				-0.2	A
Forward Voltage ¹	V _{SD}	I _F = -450mA, V _{GS} = 0V			-1.2	V
Reverse Recovery Time	t _{rr}	I _F = -1A , dI/dt = 100A / μS		46		nS
Reverse Recovery Charge	Q _{rr}			28		nC

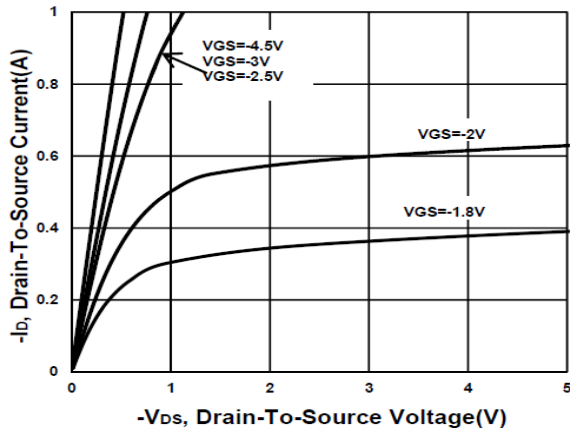
¹Pulse test : Pulse Width $\leq 300 \mu\text{sec}$, Duty Cycle $\leq 2\%$.

²Independent of operating temperature.

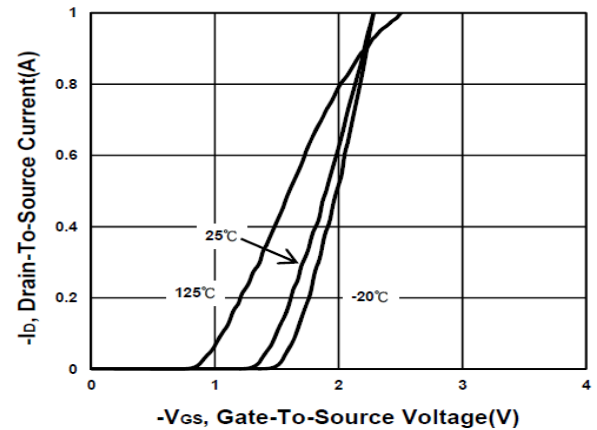
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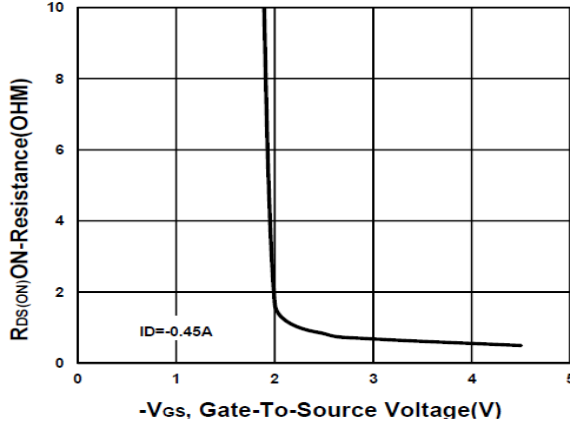
Output Characteristics



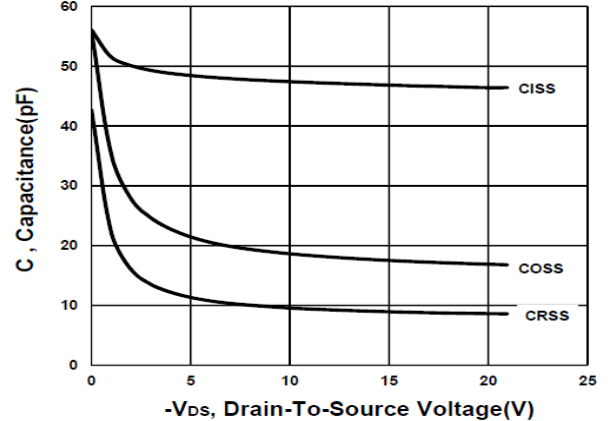
Transfer Characteristics



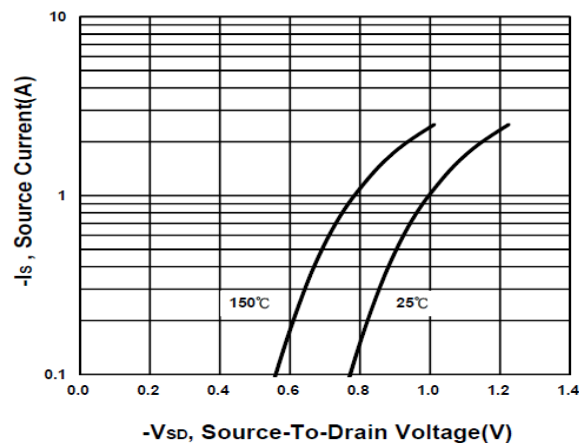
On-Resistance VS Gate-To-Source



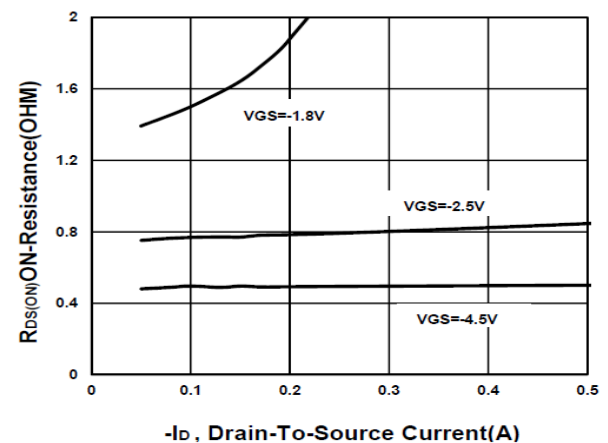
Capacitance Characteristic



Source-Drain Diode Forward Voltage

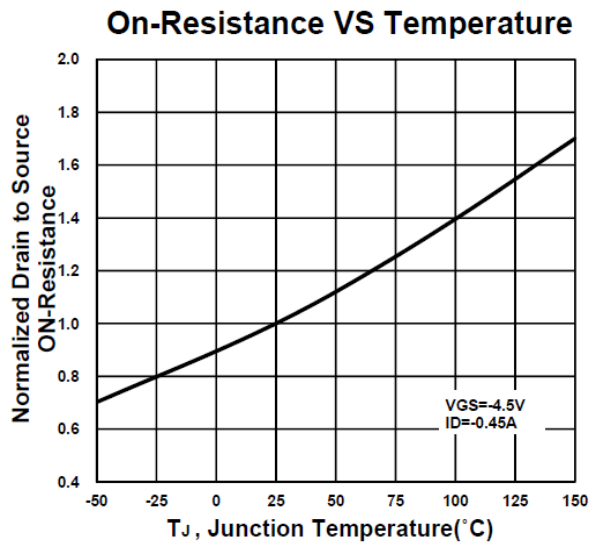


On-Resistance VS Drain Current



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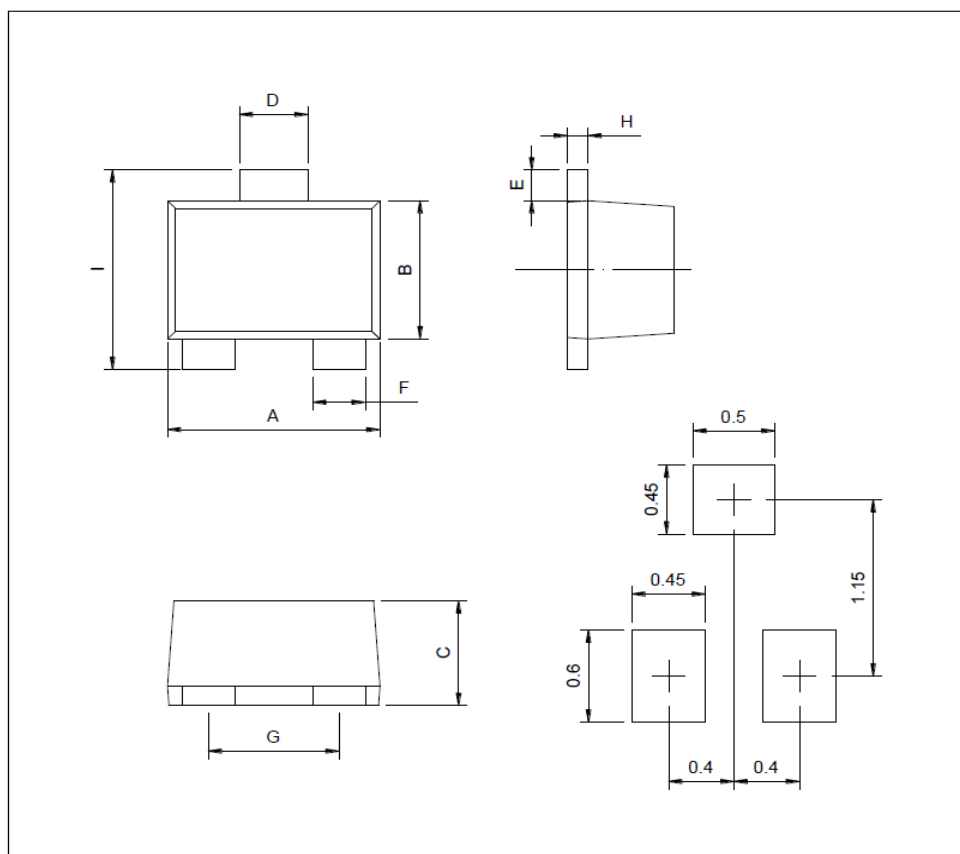
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Package Dimension

SOT-723 MECHANICAL DATA

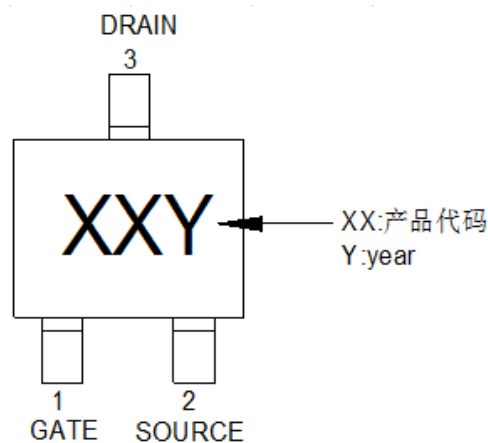
Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	1.10		1.30	H	0.10Typical		
B	0.70		0.90	I	1.10		1.30
C	0.54Max						
D	0.22		0.42				
E	0.10		0.30				
F	0.12		0.32				
G	0.80Typical						



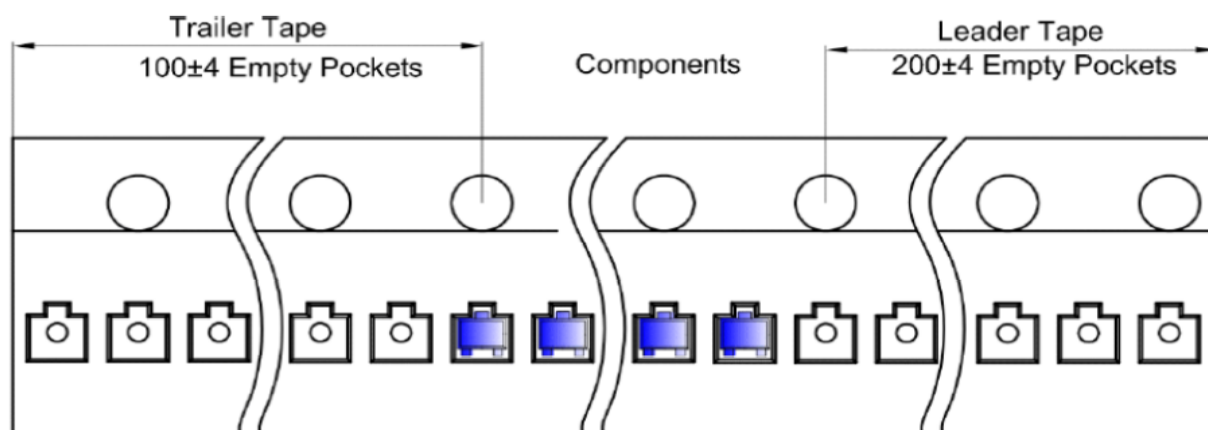
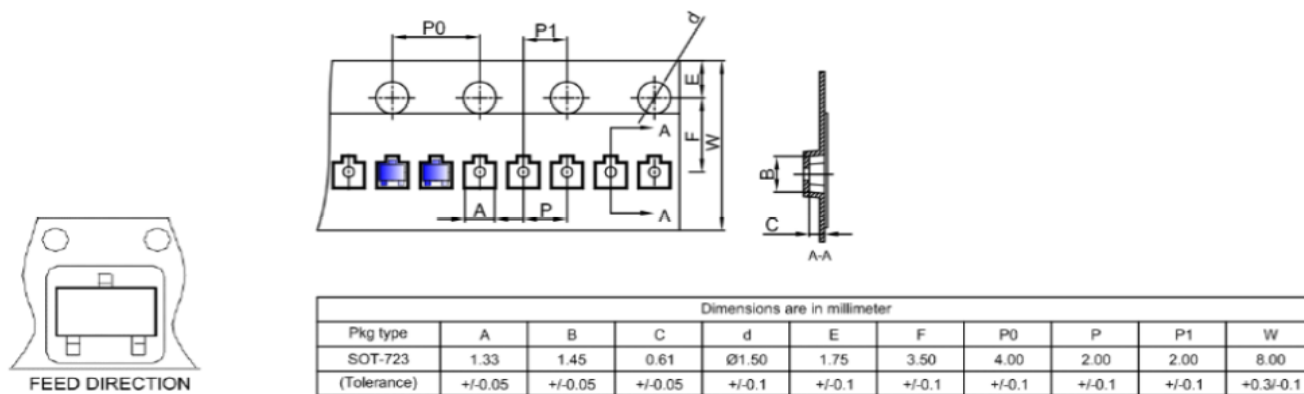
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A. Marking Information(产品代码为: 02)

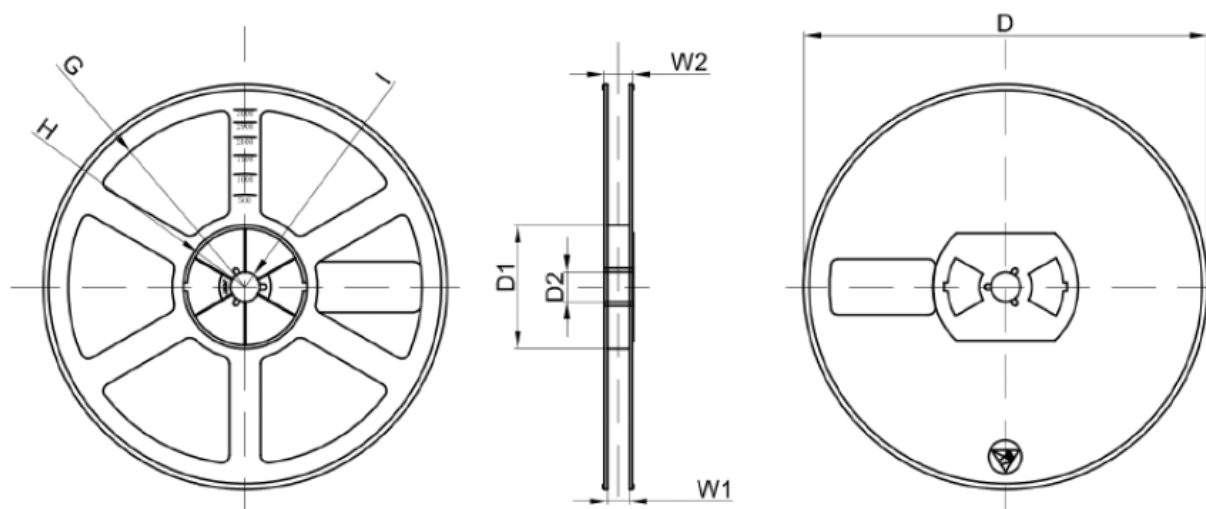


B. Tape&Reel Information:8000pcs/Reel



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Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
7"Dia	Ø178.00	54.40	13.00	R78.00	R25.60	R6.50	9.50	12.30
Tolerance	+/-2	+/-1	+/-1	+/-1	+/-1	+/-1	+/-1	+/-1

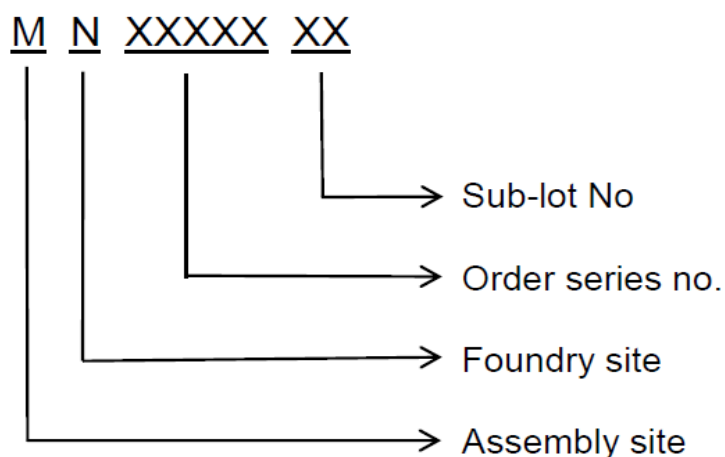
REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
8000 pcs	7 inch	120,000 pcs	203×203×195	480,000 pcs	438×438×220	

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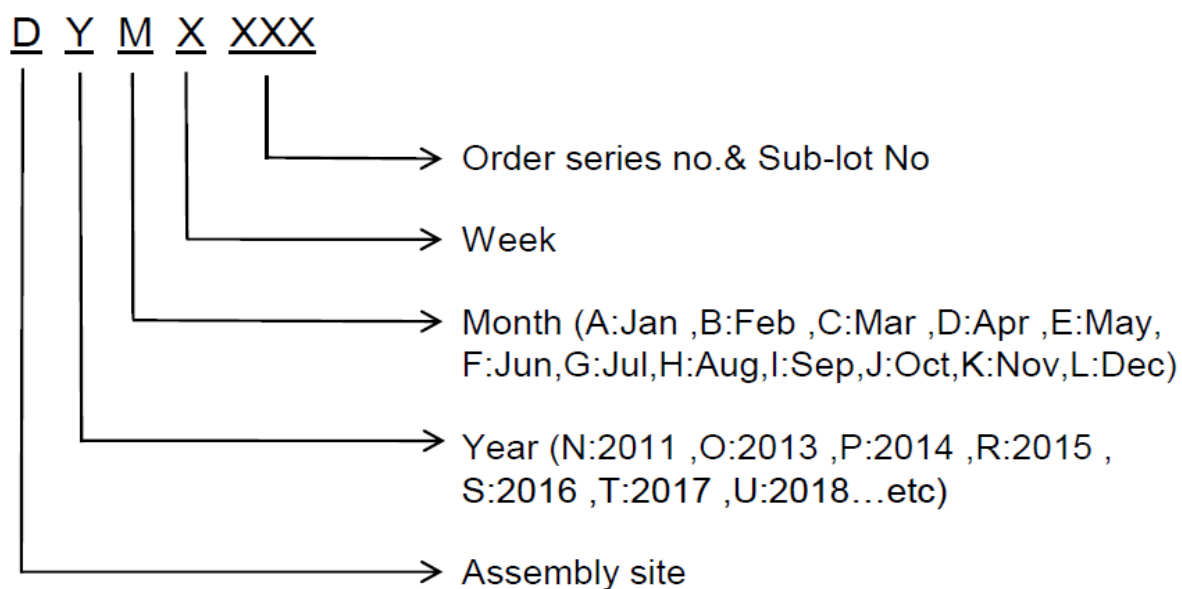
P-Channel Enhancement Mode MOSFET

C. Lot No.&Date Code rule

1.Lot No.



2.Date Code



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D.Label rule

标签内容(Label content)



1	Label Size	30 * 90 mm
2	Font style	Times New Roman or Arial (或可区分英文” 0” 和数字” 0” , ” G 和” Q” 的字型即可)
3	Great Power	Height: 4 mm
4	Package	Height: 2 mm
5	Date	Height: 2 mm Shipping date: YYYY/MM/DD, ex. 2008/09/12
6	Device	Height: 3 mm (Max: 16 Digit)
7	Lot	Height: 3 mm (Max: 9 Digit) Sub lot
8	D/C	Height: 3 mm (Max: 7 Digit)
9	QTY	Height: 3 mm (Max: 6 Digit) Thousand mark is no needed
10	Pb Free label	 Diameter: 1 cm bottom color: Green Font color: Black Font style: Arial
11	Halogen Free label	 Diameter: 1 cm bottom color: Green Font color: Black Font style: Arial
12	Scan info	Device / Lot / D/C / QTY , Insert “ / “ between every parts. for example: P3055LDG/G12345601/GGG2301/2000 DPI (Dots per inch): Over 300 dpi Code : Code 128 Height: 6 mm at least